# imall

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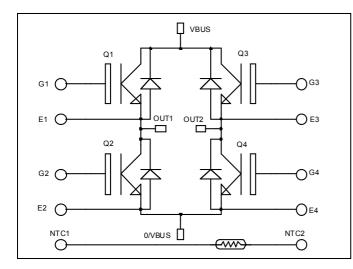
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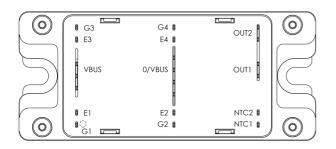




## APTGF75H120TG

## Full - Bridge NPT IGBT Power Module





## Absolute maximum ratings

Symbol	Parameter		Max ratings	Unit
V <sub>CES</sub>	Collector - Emitter Breakdown Voltage		1200	V
т	Continuous Collector Current	$T_c = 25^{\circ}C$	100	
I <sub>C</sub>	Continuous Conector Current	$T_c = 80^{\circ}C$	75	А
I <sub>CM</sub>	Pulsed Collector Current	$T_c = 25^{\circ}C$	150	
V <sub>GE</sub>	Gate – Emitter Voltage		±20	V
PD	Maximum Power Dissipation	$T_c = 25^{\circ}C$	500	W
RBSOA	Reverse Bias Safe Operating Area	$T_{j} = 150^{\circ}C$	150A @ 1200V	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on www.microsemi.com

## $V_{CES} = 1200V$ $I_{C} = 75A$ (a) $Tc = 80^{\circ}C$

#### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

#### Features

- Non Punch Through (NPT) Fast IGBT
  - Low voltage drop
    - Low tail current
  - Switching frequency up to 50 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated
- Kelvin emitter for easy drive
- Very low stray inductance
  - Symmetrical design
  - Lead frames for power connections
- Internal thermistor for temperature monitoring
- High level of integration

#### Benefits

- Outstanding performance at high frequency operation
- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Solderable terminals both for power and signal for easy PCB mounting
- Easy paralleling due to positive T<sub>C</sub> of V<sub>CEsat</sub>
- Low profile
- RoHS compliant



### All ratings (a) $T_j = 25^{\circ}C$ unless otherwise specified

## **Electrical Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
т	Zero Gate Voltage Collector Current	$V_{GE} = 0V$	$T_j = 25^{\circ}C$			250	۸
I <sub>CES</sub>	Zero Gate voltage Conector Current	$V_{CE} = 1200V$	$T_j = 125^{\circ}C$			500	μA
V	Collector Emitter acturation Voltage	$V_{GE} = 15V$	$T_j = 25^{\circ}C$		3.2	3.7	V
V <sub>CE(sat)</sub>	Collector Emitter saturation Voltage	$I_C = 75A$	$T_{j} = 125^{\circ}C$		3.9		v
V <sub>GE(th)</sub>	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 2.5 \text{ mA}$		4.5		6.5	V
I <sub>GES</sub>	Gate – Emitter Leakage Current	$V_{GE} = \pm 20V, V_{CE} = 0V$				±500	nA

## **Dynamic Characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
Cies	Input Capacitance	$V_{GE} = 0V$			5.1		
Coes	Output Capacitance	$V_{CE} = 25V$			0.7		nF
C <sub>res</sub>	Reverse Transfer Capacitance	f = 1 MHz		0.4			
Q <sub>G</sub>	Gate charge	V <sub>GE</sub> =±15V, I <sub>C</sub> =75 V <sub>CE</sub> =600V	$V_{GE}$ =±15V, I <sub>C</sub> =75A $V_{CE}$ =600V		0.8		μC
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (25°C)			120		
Tr	Rise Time	$V_{GE} = 15V$			50		ns
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 600V$ $I_C = 75A$			310		
$T_{\rm f}$	Fall Time	$R_{G} = 7.5\Omega$			20		
T <sub>d(on)</sub>	Turn-on Delay Time	Inductive Switching (125°C)			130		
Tr	Rise Time	$V_{GE} = 15V$			60		ns
T <sub>d(off)</sub>	Turn-off Delay Time	$V_{Bus} = 600V$ $I_{C} = 75A$			360		
T <sub>f</sub>	Fall Time	$R_G = 7.5\Omega$			30		
Eon	Turn-on Switching Energy	$\begin{array}{c} V_{GE} = \pm 15V \\ V_{Bus} = 600V \end{array} T$	$T_j = 125^{\circ}C$		9		mJ
E <sub>off</sub>	Turn-off Switching Energy	$I_{C} = 75A$ $R_{G} = 7.5\Omega$ T	$T_j = 125^{\circ}C$		4		1113
I <sub>sc</sub>	Short Circuit data	$V_{GE} \le 15V$ ; $V_{Bus} = t_p \le 10 \mu s$ ; $T_1 = 12$			450		А

### **Reverse diode ratings and characteristics**

Symbol	Characteristic	Test Conditions		Min	Тур	Max	Unit
V <sub>RRM</sub>	Maximum Peak Repetitive Reverse Voltage			1200			V
I <sub>RM</sub>	Maximum Reverse Leakage Current	$V_{R} = 1200 V$	$T_j = 25^{\circ}C$			250	μA
-KW		· K ·····	$T_{j} = 125^{\circ}C$			500	P** -
$I_{\rm F}$	DC Forward Current		$Tc = 80^{\circ}C$		50		А
V		$T_j = 25^{\circ}C$		2.1		v	
$V_{\rm F}$	Diode Forward Voltage	$I_F = 50A$	$T_{j} = 125^{\circ}C$		1.9		v
+	Reverse Recovery Time $T_j = 25^{\circ}C$ $T_j = 125^{\circ}C$		$T_j = 25^{\circ}C$		95		
t <sub>rr</sub>				190		ns	
0	Parama Pasavani Changa	$I_{F} = 50A$ $V_{R} = 600V$ $di/dt = 1500A/\mu s$	$T_j = 25^{\circ}C$		4.2		чС
Q <sub>rr</sub>	Reverse Recovery Charge		$T_{j} = 125^{\circ}C$		9		μC
Г			$T_j = 25^{\circ}C$		1.5		mI
Er	Reverse Recovery Energy		$T_j = 125^{\circ}C$		3		mJ



## APTGF75H120TG

### Temperature sensor NTC (see application note APT0406 on www.microsemi.com for more information).

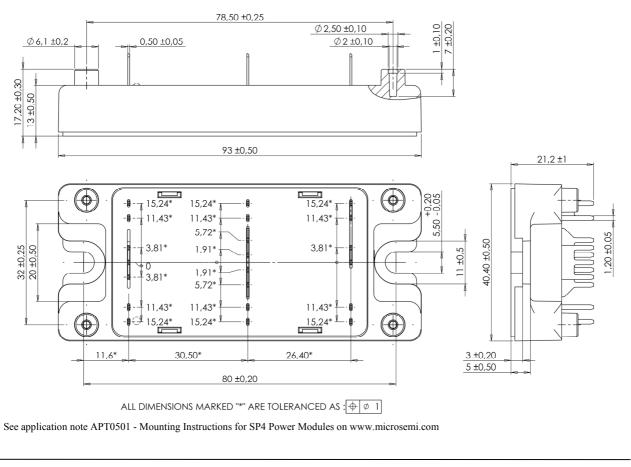
Symbol	Characteristic		Min	Тур	Max	Unit
R <sub>25</sub>	Resistance @ 25°C			50		kΩ
$\Delta R_{25}/R_{25}$				5		%
B <sub>25/85</sub>	$T_{25} = 298.15 \text{ K}$			3952		K
$\Delta B/B$		T <sub>C</sub> =100°C		4		%
	B					

 $R_{T} = \frac{R_{25}}{\exp\left[B_{25/85}\left(\frac{1}{T_{25}} - \frac{1}{T}\right)\right]}$  T: Thermistor temperature R<sub>T</sub>: Thermistor value at T

### Thermal and package characteristics

Symbol	Characteristic			Min	Тур	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance		IGBT			0.25	°C/W
			Diode			0.6	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t =1 min, 50/60Hz			4000			V
T <sub>J</sub>	Operating junction temperature range			-40		150	
T <sub>STG</sub>	Storage Temperature Range		-40		125	°C	
T <sub>C</sub>	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M5	2.5		4.7	N.m
Wt	Package Weight					160	g

### SP4 Package outline (dimensions in mm)

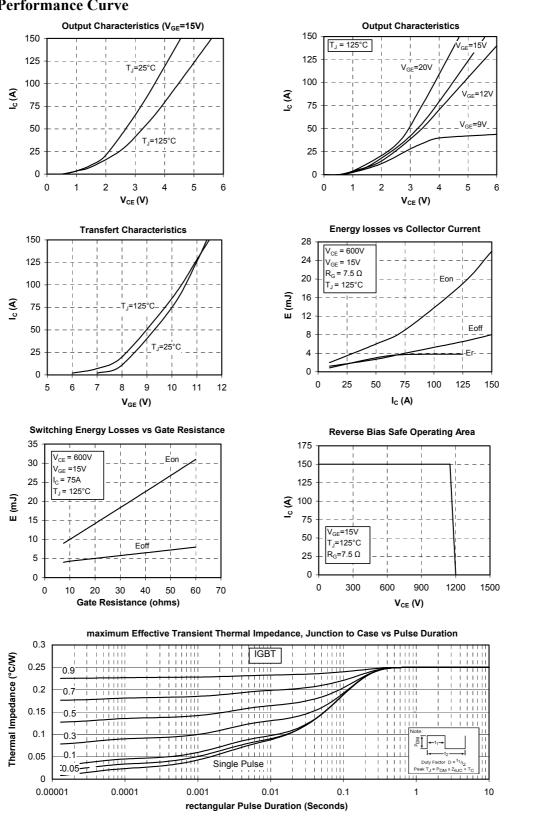


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#### **Typical Performance Curve**



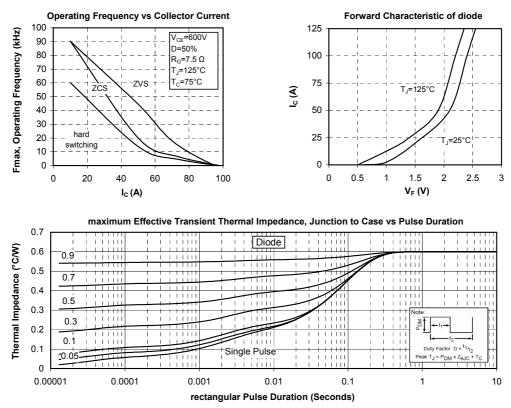


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